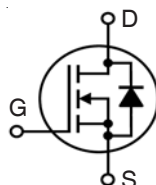


X3-Class HiPerFET™ Power MOSFET

IXFP56N30X3M

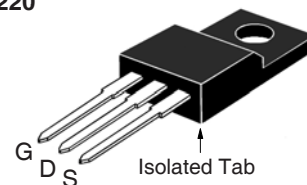
(Electrically Isolated Tab)

N-Channel Enhancement Mode



$$\begin{aligned} V_{DSS} &= 300V \\ I_{D25} &= 56A \\ R_{DS(on)} &\leq 27m\Omega \end{aligned}$$

OVERMOLDED
TO-220



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	300	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	300	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$, Limited by T_{JM}	56	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	112	A
I_A	$T_C = 25^\circ\text{C}$	28	A
E_{AS}	$T_C = 25^\circ\text{C}$	700	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	50	V/ns
P_D	$T_C = 25^\circ\text{C}$	36	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
M_d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		2.5	g

Features

- International Standard Package
- Plastic Overmolded Tab
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- 2500V~ Electrical Isolation
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1.5mA$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			5 μA 500 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 28A$, Note 1		21	27 m Ω

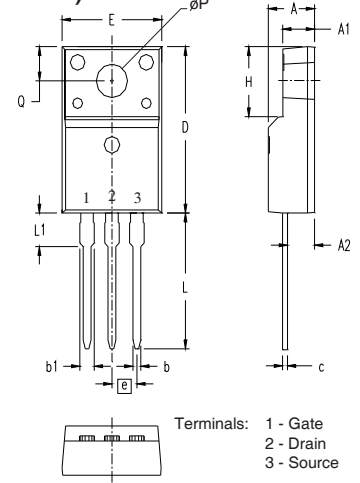
Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	V _{DS} = 10V, I _D = 28A, Note 1	26	43	S
R_{Gi}	Gate Input Resistance		2.3	Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		3750	pF
C_{oss}			560	pF
C_{rss}			3	pF
Effective Output Capacitance				
C_{o(er)}	Energy related	V_{GS} = 0V V_{DS} = 0.8 • V_{DSS}	210	pF
C_{o(tr)}	Time related		860	pF
t_{d(on)}	Resistive Switching Times V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 28A R_G = 5Ω (External)		21	ns
t_r			26	ns
t_{d(off)}			64	ns
t_f			10	ns
Q_{g(on)}	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 28A		56	nC
Q_{gs}			18	nC
Q_{gd}			17	nC
R_{thJC}				3.5 °C/W
R_{thCS}		0.50		°C/W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			56 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			224 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 28\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		115	ns
Q_{RM}			580	nC
I_{RM}			10	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

OVERMOLDED TO-220 (IXFP...M)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\emptyset P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

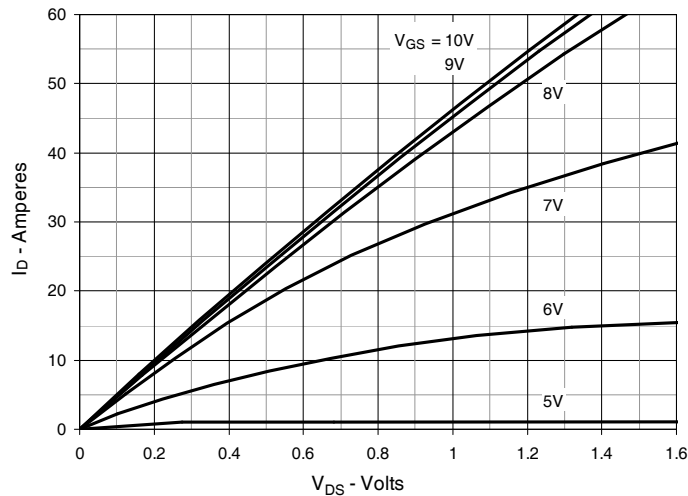
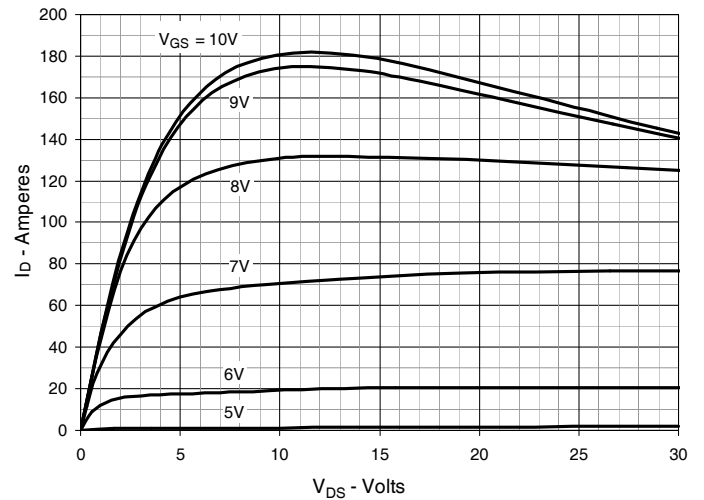
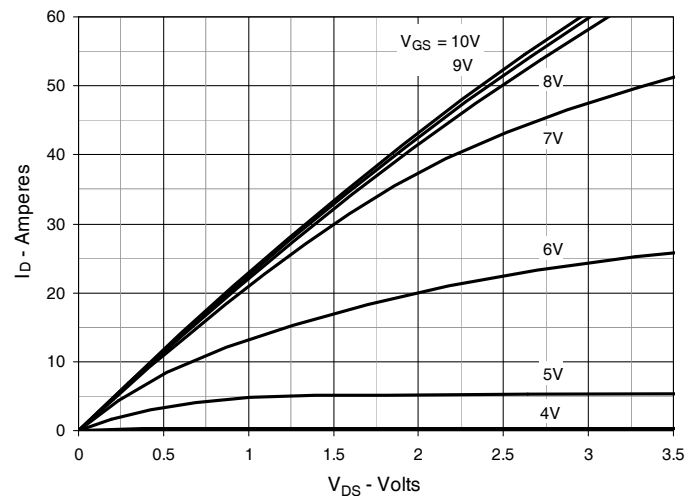
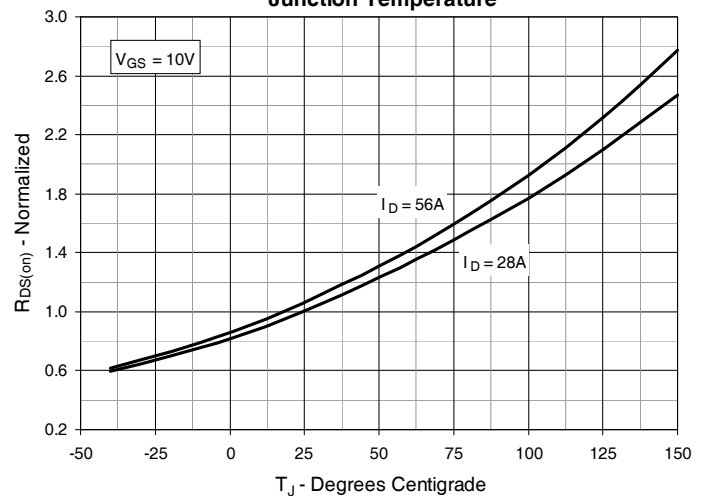
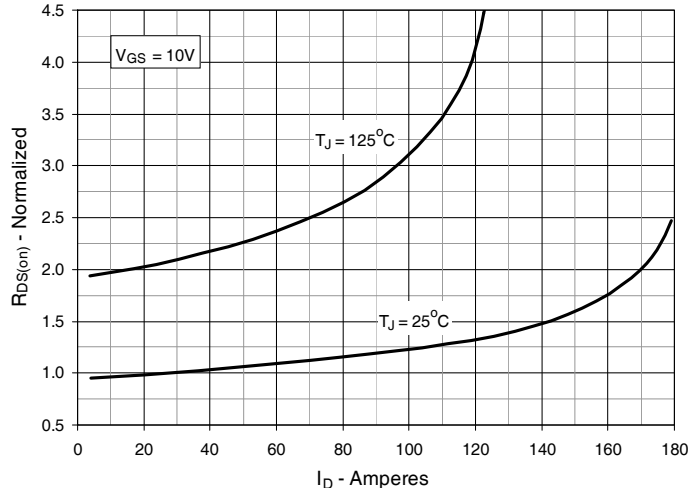
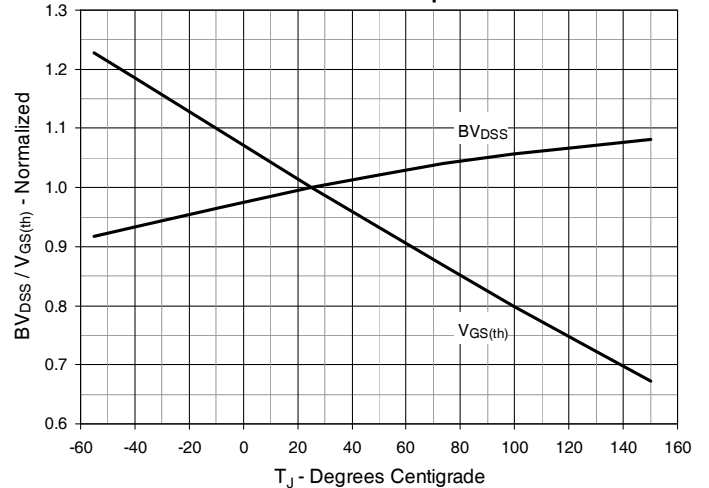
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 28\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 28\text{A}$ Value vs. Drain Current

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature


Fig. 7. Input Admittance

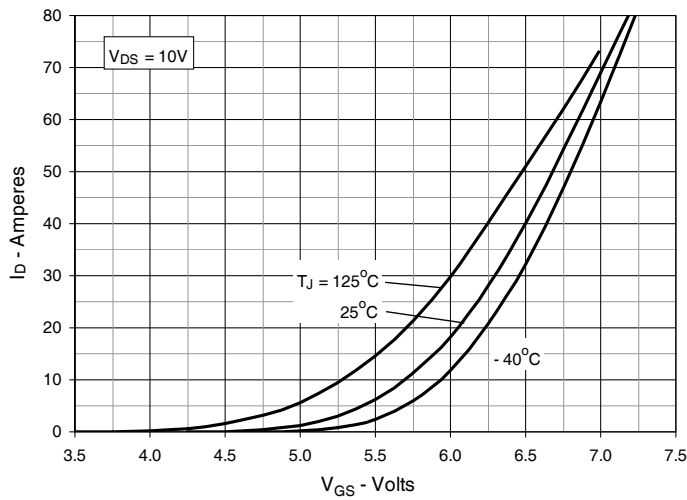


Fig. 8. Transconductance

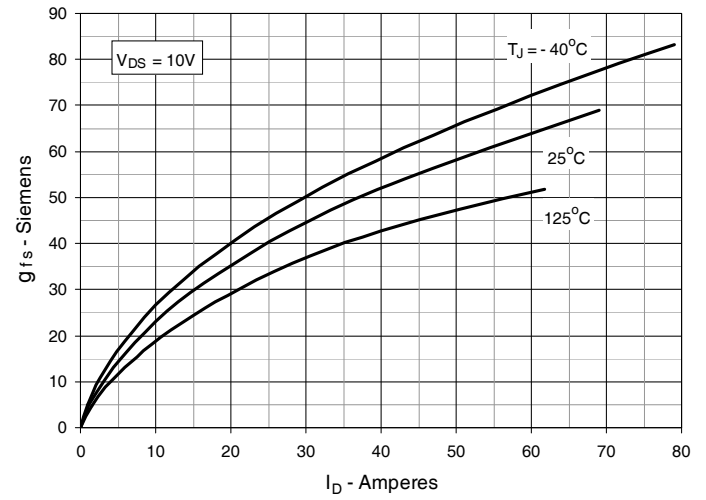


Fig. 9. Forward Voltage Drop of Intrinsic Diode

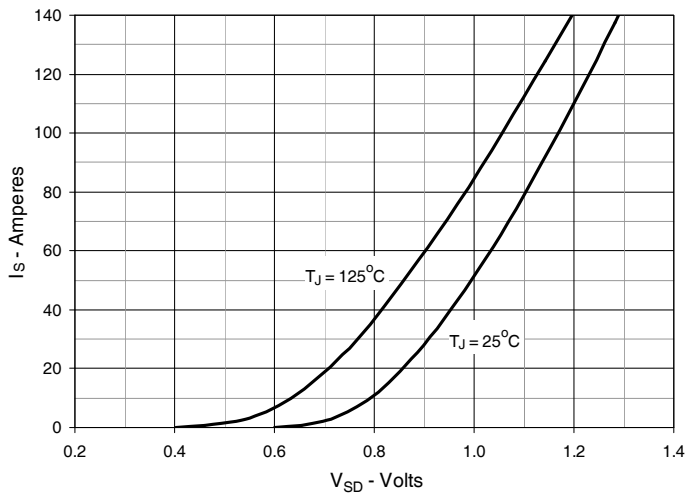


Fig. 10. Gate Charge

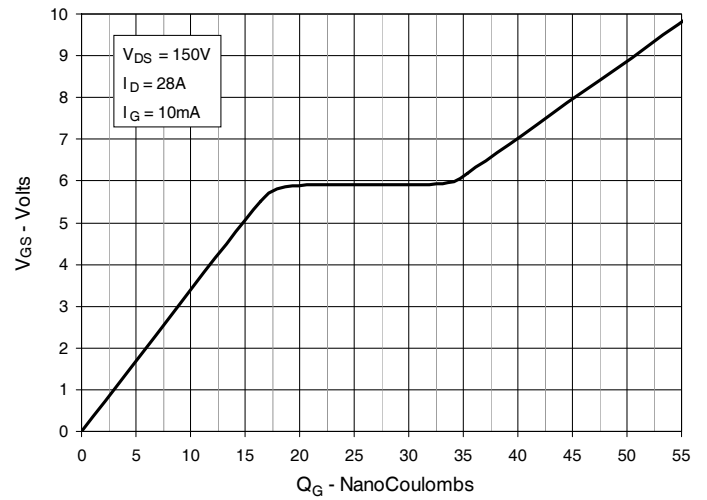


Fig. 11. Capacitance

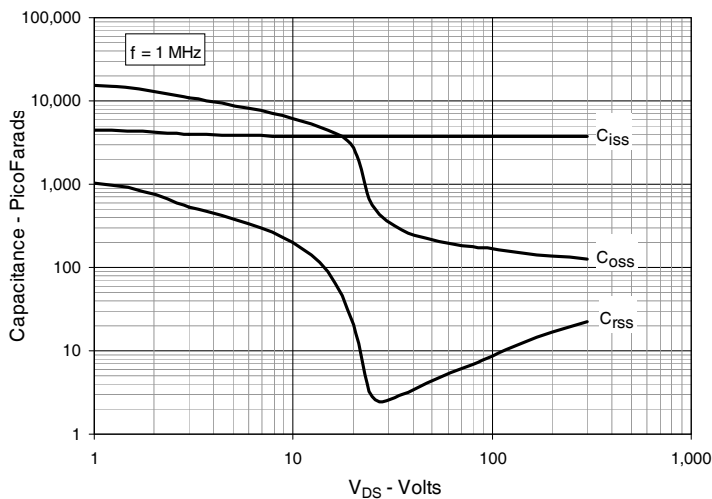


Fig. 12. Output Capacitance Stored Energy

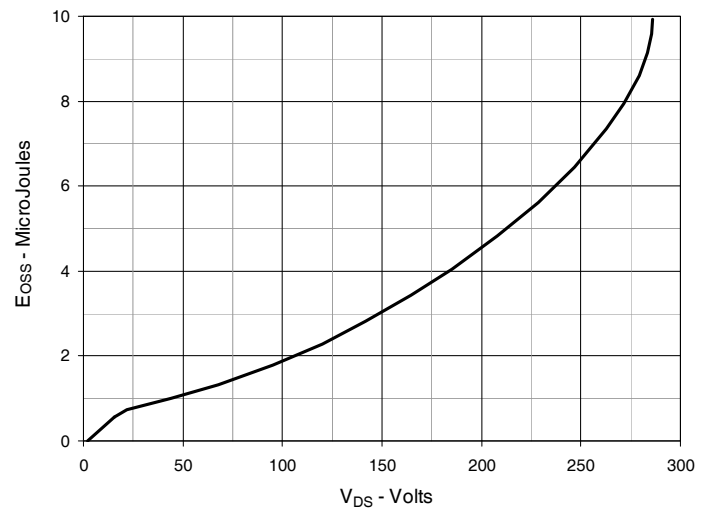
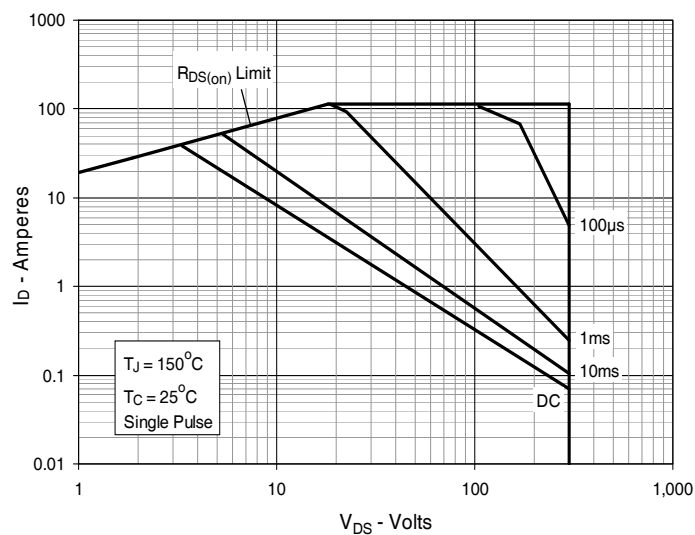


Fig. 13. Forward-Bias Safe Operating Area

Fig. 14. Maximum Transient Thermal Impedance
